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Tel: +86-755-8981 8866 Fax: +86-755-8427 6832
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Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China

EPC2100 – Enhancement-Mode GaN Power Transistor Half-Bridge

V_{DS} , 30 V
$R_{DS(on)}$, 8.2 mΩ (Q1), 2.1 mΩ (Q2)
I_D , 10 A (Q1), 40 A (Q2)

EFFICIENT POWER CONVERSION

RoHS Pb Halogen-Free

Gallium Nitride's exceptionally high electron mobility and low temperature coefficient allows very low $R_{DS(on)}$, while its lateral device structure and majority carrier diode provide exceptionally low Q_G and zero Q_{RR}. The end result is a device that can handle tasks where very high switching frequency, and low on-time are beneficial as well as those where on-state losses dominate.

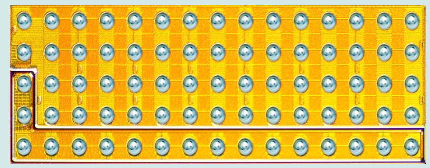
Maximum Ratings

DEVICE	PARAMETER		VALUE	UNIT
Q1	V_{DS}	Drain-to-Source Voltage (Continuous)	30	V
		Drain-to-Source Voltage (up to 10,000 5 ms pulses at 150°C)	36	
	I_D	Continuous (T_A = 25˚C, $R_{θJA}$ = 92°C/W)	10	A
		Pulsed (25°C, T_{PULSE} = 300 µs)	100	
	V_{GS}	Gate-to-Source Voltage	6	V
		Gate-to-Source Voltage	-4	
	T_J	Operating Temperature	–40 to 150	°C
	T_{STG}	Storage Temperature	–40 to 150	
Q2	V_{DS}	Drain-to-Source Voltage (Continuous)	30	V
		Drain-to-Source Voltage (up to 10,000 5 ms pulses at 150°C)	36	
	I_D	Continuous (T_A = 25˚C, $R_{θJA}$ = 22°C/W)	40	A
		Pulsed (25°C, T_{PULSE} = 300 µs)	400	
	V_{GS}	Gate-to-Source Voltage	6	V
		Gate-to-Source Voltage	-4	
	T_J	Operating Temperature	–40 to 150	°C
	T_{STG}	Storage Temperature	–40 to 150	

Thermal Characteristics

PARAMETER		TYP	UNIT
$R_{θJC}$	Thermal Resistance, Junction to Case	0.4	°C/W
$R_{θJB}$	Thermal Resistance, Junction to Board	2.5	
$R_{θJA}$	Thermal Resistance, Junction to Ambient (Note 1)	42	

Note 1: $R_{θJA}$ is determined with the device mounted on one square inch of copper pad, single layer 2 oz copper on FR4 board.
See http://epc-co.com/epc/documents/product-training/Appnote_Thermal_Performance_of_eGaN_FETs.pdf for details



EPC2100 eGaN® ICs are supplied only in passivated die form with solder bumps
Die Size: 6.05 mm x 2.3 mm

Applications

- High Frequency DC-DC
- Point-of-Load (POL) Converters

Benefits

- High Frequency Operation
- Ultra High Efficiency
- High Density Footprint

www.epc-co.com/epc/Products/eGaNFETsandICs/EPC2100.aspx

Static Characteristics							
DEVICE	PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
Q1	BV_{DSS}	Drain-to-Source Voltage	V_{GS} = 0 V, I_D = 0.3 mA	30			V
	I_{DSS}	Drain-Source Leakage	V_{DS} = 24 V, V_{GS} = 0 V		0.004	0.2	mA
	I_{GSS}	Gate-to-Source Forward Leakage	V_{GS} = 5 V		0.007	3	mA
		Gate-to-Source Reverse Leakage	V_{GS} = -4 V		0.004	0.2	mA
	$V_{GS(TH)}$	Gate Threshold Voltage	V_{DS} = V_{GS}, I_D = 4 mA	0.8	1.3	2.5	V
	$R_{DS(on)}$	Drain-Source On Resistance	V_{GS} = 5 V, I_D = 25 A		6	8.2	mΩ
	V_{SD}	Source-Drain Forward Voltage	I_S = 0.5 A, V_{GS} = 0 V		1.8		V
Q2	BV_{DSS}	Drain-to-Source Voltage	V_{GS} = 0 V, I_D = 1 mA	30			V
	I_{DSS}	Drain-Source Leakage	V_{DS} = 24 V, V_{GS} = 0 V		0.015	0.8	mA
	I_{GSS}	Gate-to-Source Forward Leakage	V_{GS} = 5 V		0.03	9	mA
		Gate-to-Source Reverse Leakage	V_{GS} = -4 V		0.015	0.8	mA
	$V_{GS(TH)}$	Gate Threshold Voltage	V_{DS} = V_{GS}, I_D = 16 mA	0.8	1.3	2.5	V
	$R_{DS(on)}$	Drain-Source On Resistance	V_{GS} = 5 V, I_D = 25 A		1.5	2.1	mΩ
	V_{SD}	Source-Drain Forward Voltage	I_S = 0.5 A, V_{GS} = 0 V		1.7		V

Dynamic Characteristics							
DEVICE	PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
Q1	C_{ISS}	Input Capacitance	V_{DS} = 15 V, V_{GS} = 0 V		395	475	pF
	C_{RSS}	Reverse Transfer Capacitance			15		
	C_{OSS}	Output Capacitance			290	435	
	$C_{OSS(ER)}$	Effective Output Capacitance, Energy Related (Note 2)	V_{DS} = 0 to 15 V, V_{GS} = 0 V		371		
	$C_{OSS(TR)}$	Effective Output Capacitance, Time Related (Note 3)			404		
	Q_G	Total Gate Charge	V_{DS} = 15 V, V_{GS} = 5 V, I_D = 25 A		3.6	4.9	nC
	Q_{GS}	Gate-to-Source Charge	V_{DS} = 15 V, I_D = 25 A		1.3		
	Q_{GD}	Gate-to-Drain Charge			0.6		
	$Q_{G(TH)}$	Gate Charge at Threshold			0.9		
	Q_{OSS}	Output Charge	V_{DS} = 15 V, V_{GS} = 0 V		6.1	9.2	
	Q_{RR}	Source-Drain Recovery Charge			0		
Q2	C_{ISS}	Input Capacitance	V_{DS} = 15 V, V_{GS} = 0 V		1630	1960	pF
	C_{RSS}	Reverse Transfer Capacitance			64		
	C_{OSS}	Output Capacitance			1370	2060	
	$C_{OSS(ER)}$	Effective Output Capacitance, Energy Related (Note 2)	V_{DS} = 0 to 15 V, V_{GS} = 0 V		1740		
	$C_{OSS(TR)}$	Effective Output Capacitance, Time Related (Note 3)			1900		
	Q_G	Total Gate Charge	V_{DS} = 15 V, V_{GS} = 5 V, I_D = 25 A		15	19	nC
	Q_{GS}	Gate-to-Source Charge	V_{DS} = 15 V, I_D = 25 A		4.8		
	Q_{GD}	Gate-to-Drain Charge			2.7		
	$Q_{G(TH)}$	Gate Charge at Threshold			3.4		
	Q_{OSS}	Output Charge	V_{DS} = 15 V, V_{GS} = 0 V		29	44	
	Q_{RR}	Source-Drain Recovery Charge			0		

Note 2: $C_{OSS(ER)}$ is a fixed capacitance that gives the same stored energy as C_{OSS} while V_{DS} is rising from 0 to 50% BV_{DSS}.
Note 3: $C_{OSS(TR)}$ is a fixed capacitance that gives the same charging time as C_{OSS} while V_{DS} is rising from 0 to 50% BV_{DSS}.

Figure 1a (Q1): Typical Output Characteristics at 25°C

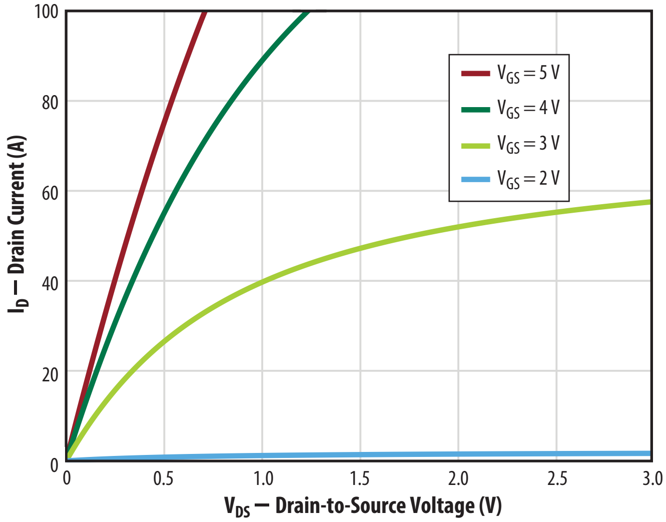


Figure 1b (Q2): Typical Output Characteristics at 25°C

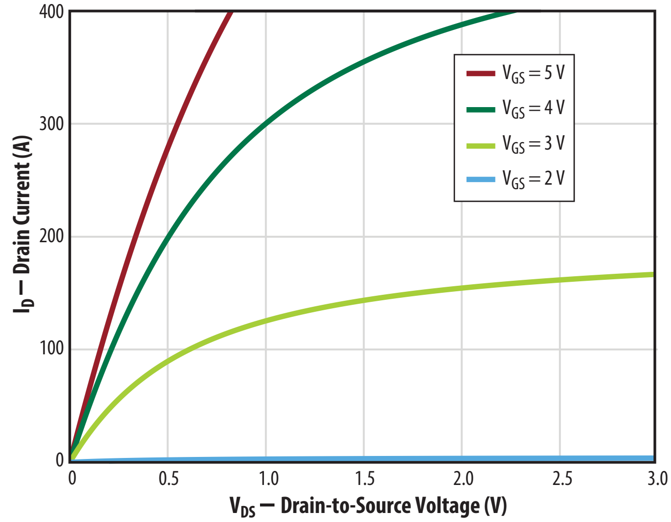


Figure 2a (Q1): Transfer Characteristics

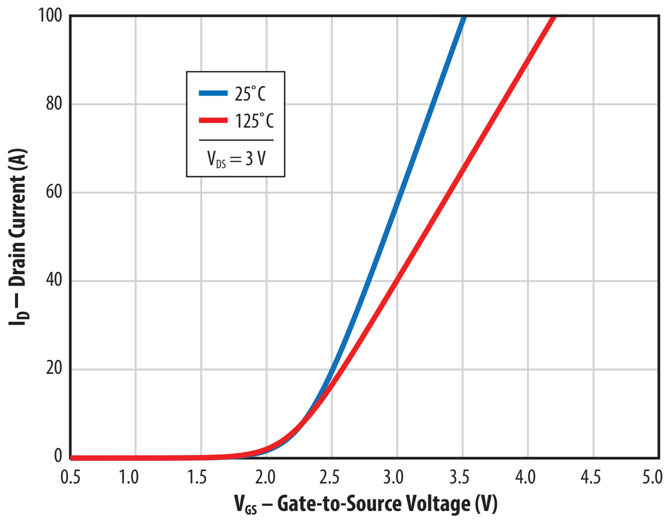


Figure 2b (Q2): Transfer Characteristics

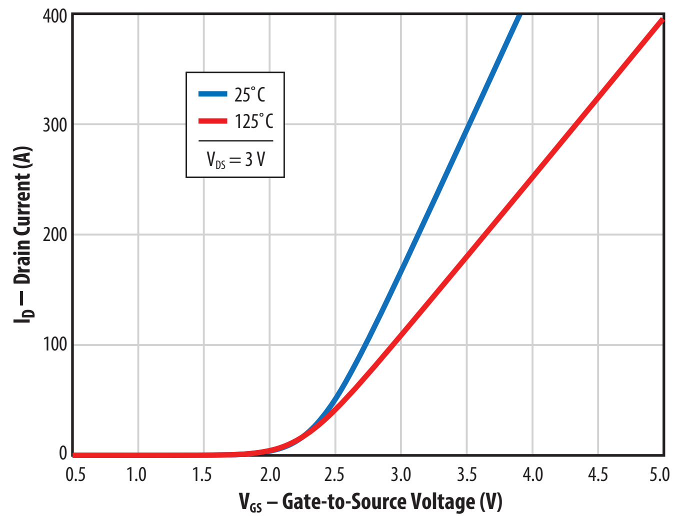


Figure 3a (Q1): $R_{DS(on)}$ vs. V_{GS} for Various Drain Currents

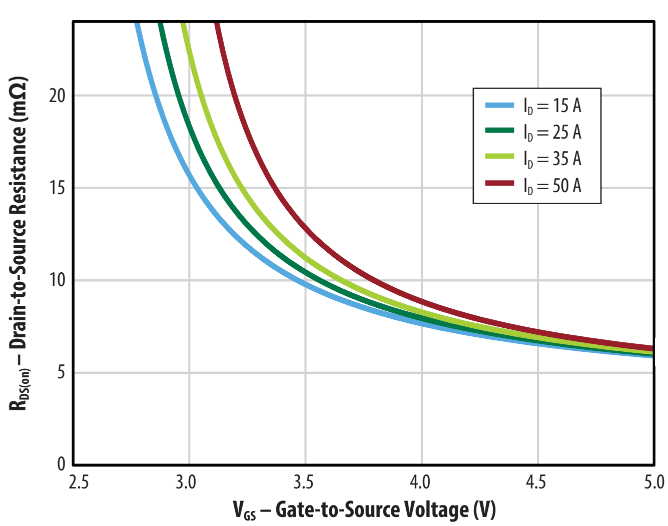


Figure 3b (Q2): $R_{DS(on)}$ vs. V_{GS} for Various Drain Currents

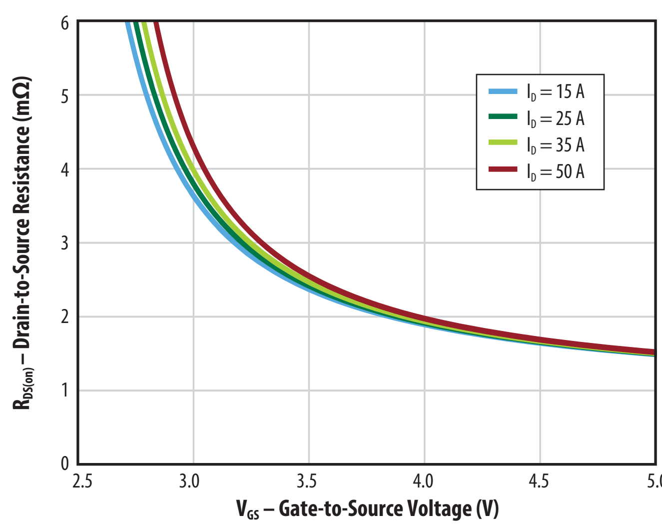


Figure 4a (Q1): $R_{DS(on)}$ vs. V_{GS} for Various Temperatures

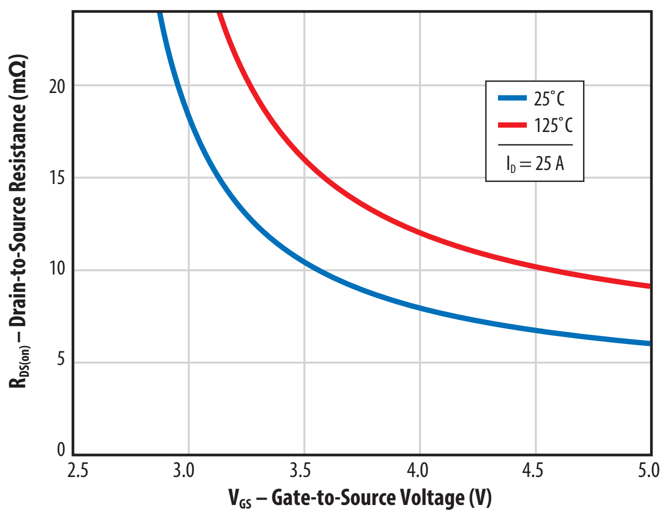


Figure 4b (Q2): $R_{DS(on)}$ vs. V_{GS} for Various Temperatures

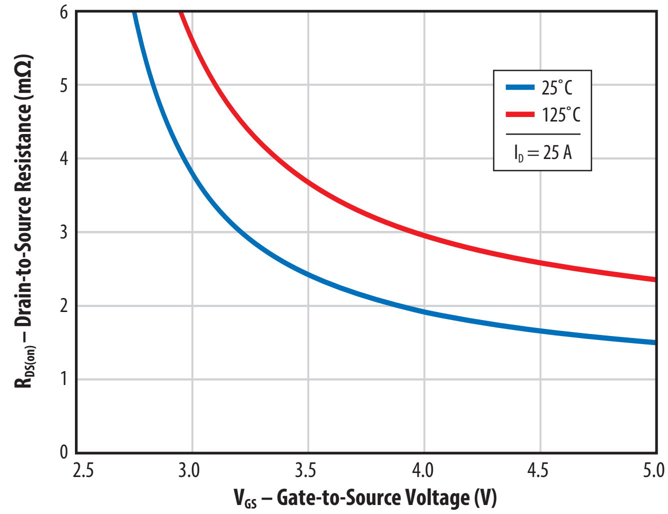


Figure 5a (Q1): Capacitance (Linear Scale)

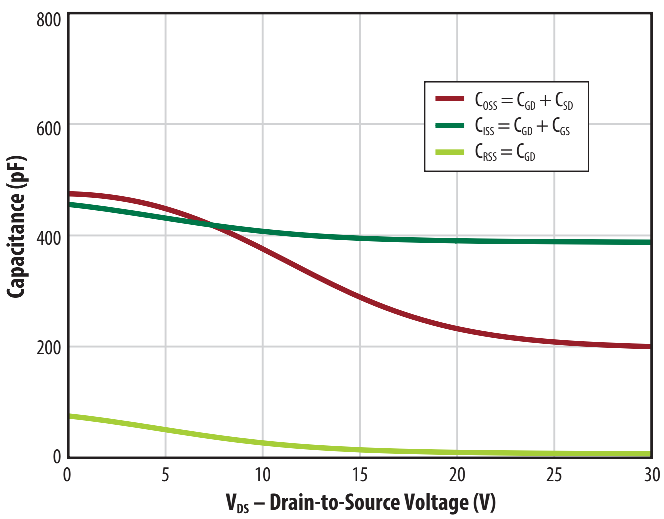


Figure 5b (Q1): Capacitance (Log Scale)

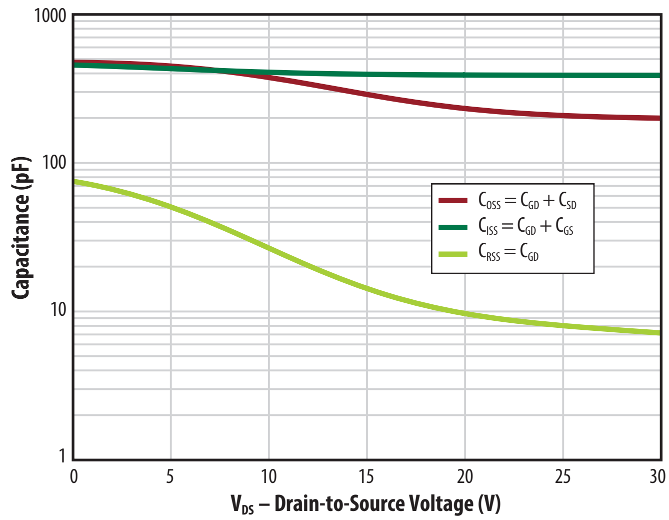


Figure 5c (Q2): Capacitance (Linear Scale)

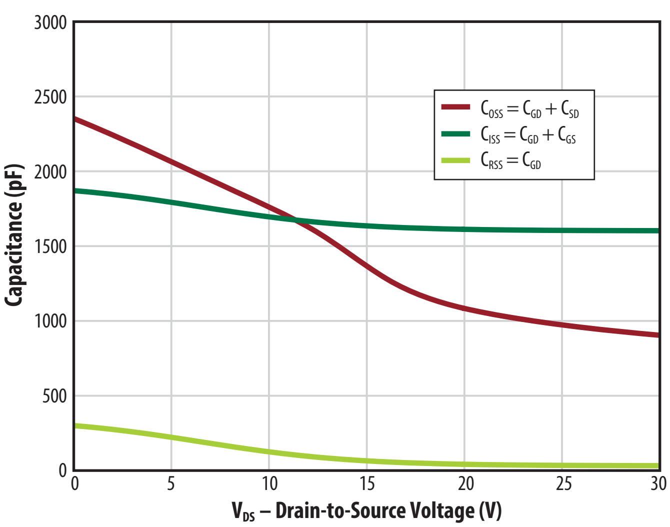


Figure 5d (Q2): Capacitance (Log Scale)

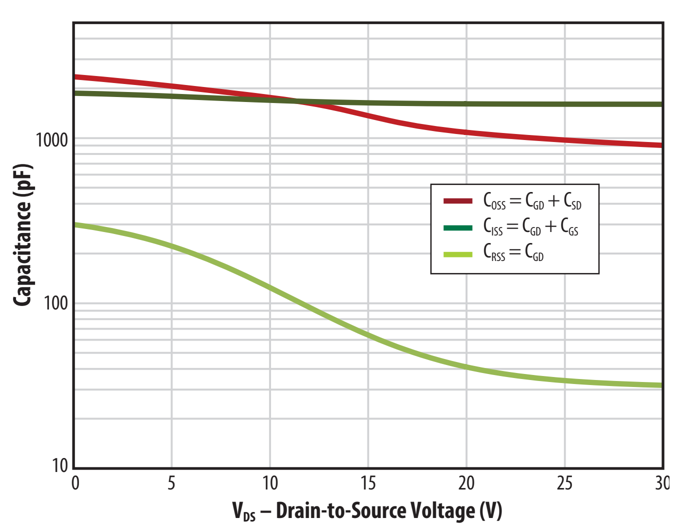


Figure 6a (Q1): Output Charge and C_{OSS} Stored Energy

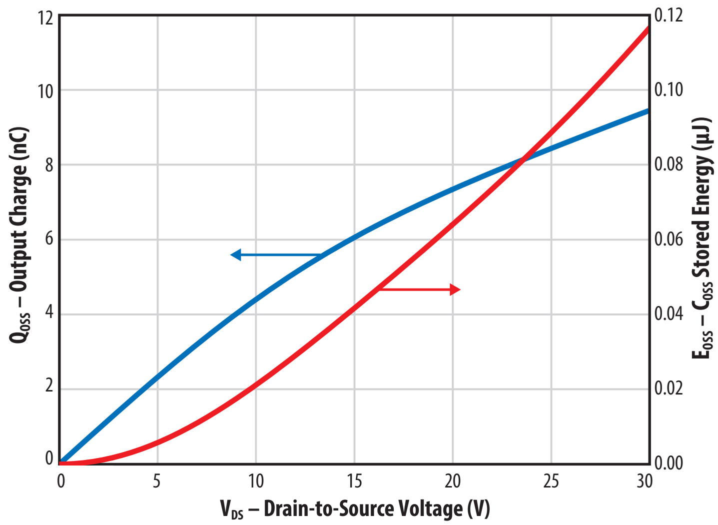


Figure 6b (Q2): Output Charge and C_{OSS} Stored Energy

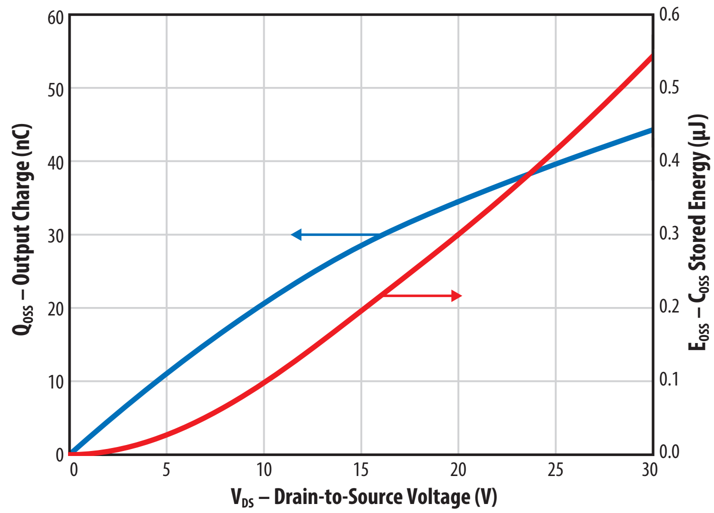


Figure 7a (Q1): Gate Charge

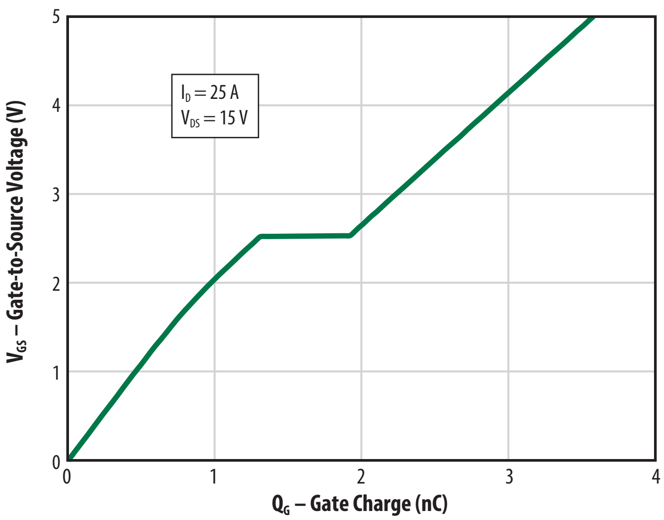


Figure 7b (Q2): Gate Charge

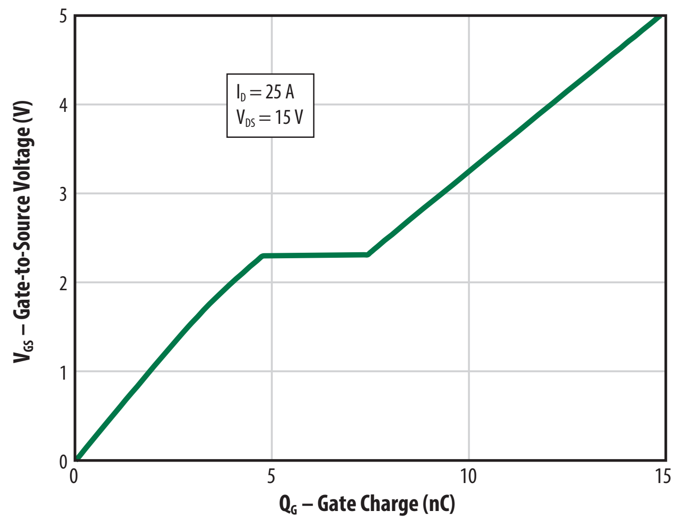


Figure 8a (Q1): Reverse Drain-Source Characteristics

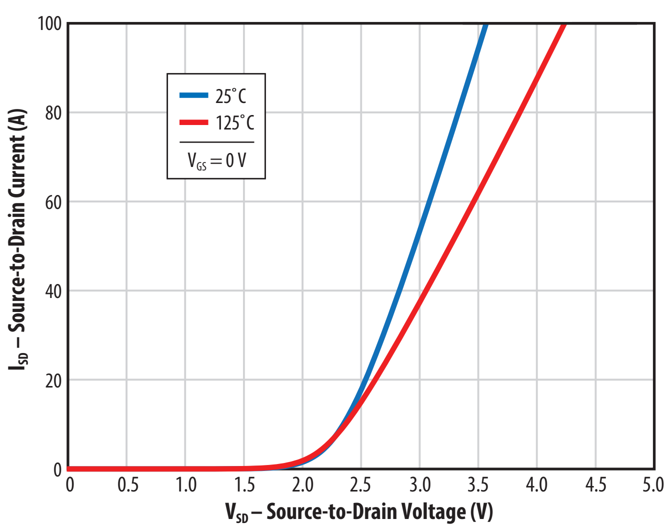


Figure 8b (Q2): Reverse Drain-Source Characteristics

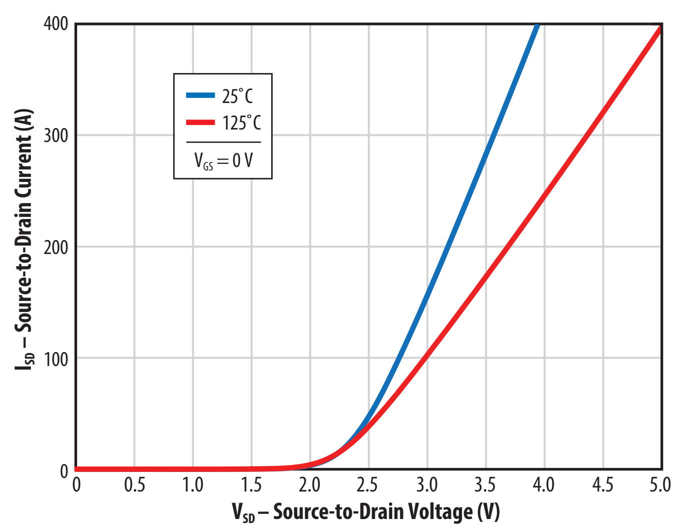


Figure 9a (Q1):
Normalized On-State Resistance vs. Temperature

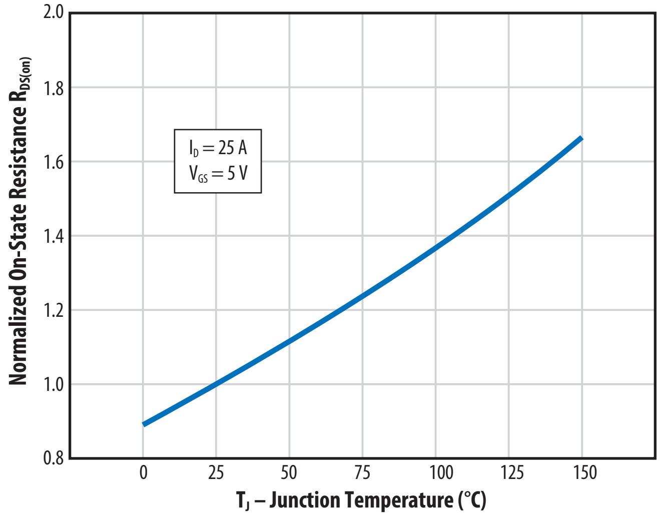


Figure 9b (Q2):
Normalized On-State Resistance vs. Temperature

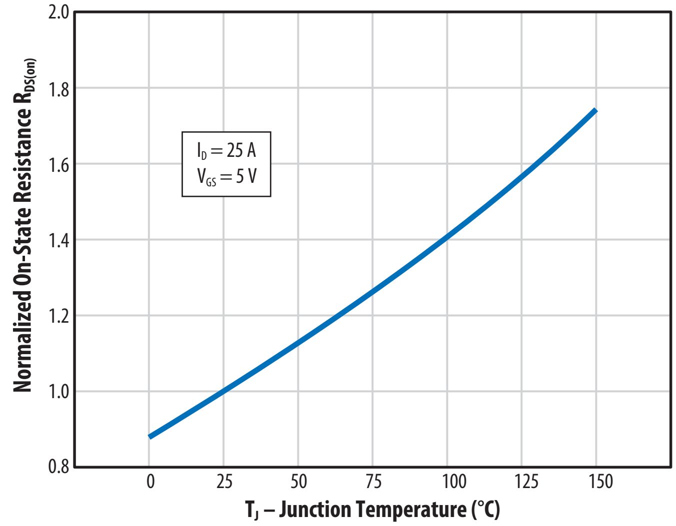


Figure 10a (Q1):
Normalized Threshold Voltage vs. Temperature

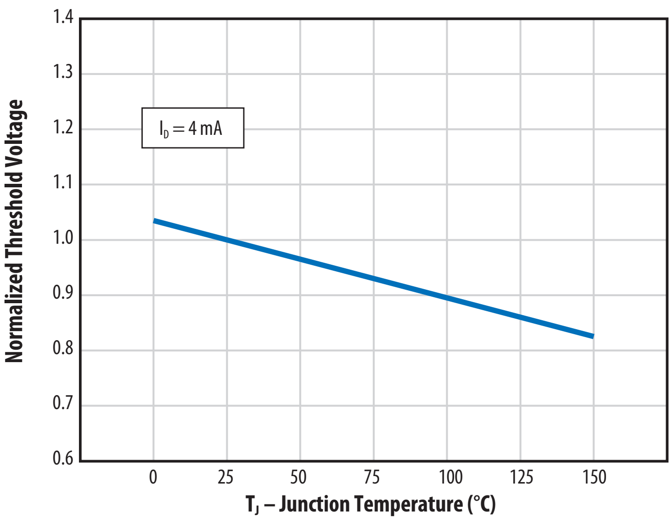


Figure 10b (Q2):
Normalized Threshold Voltage vs. Temperature

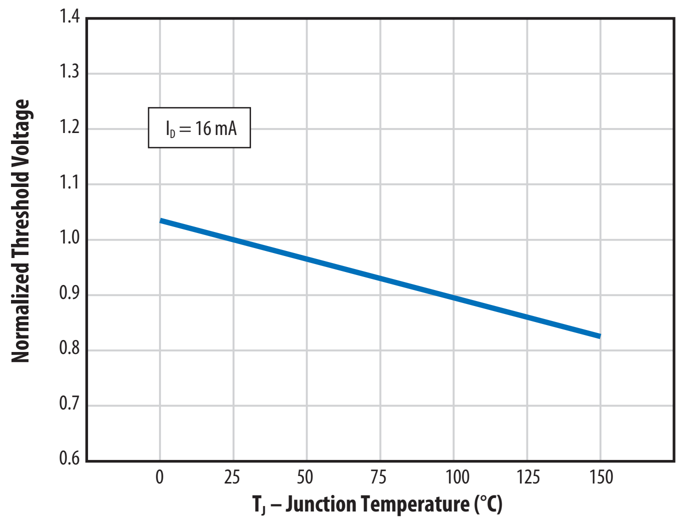


Figure 11a (Q1): Safe Operating Area

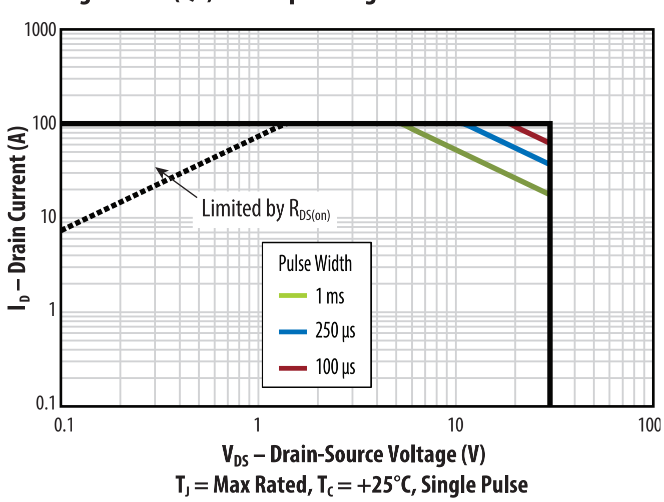


Figure 11b (Q2): Safe Operating Area

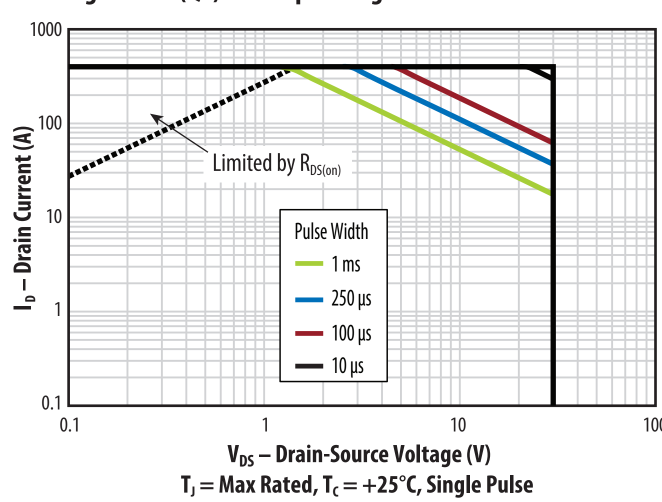


Figure 12a
Transient Thermal Response Curves

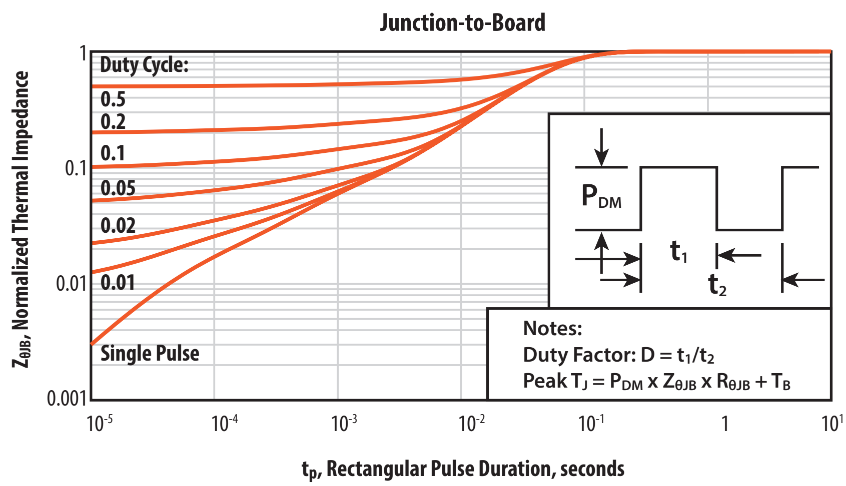


Figure 12b
Transient Thermal Response Curves

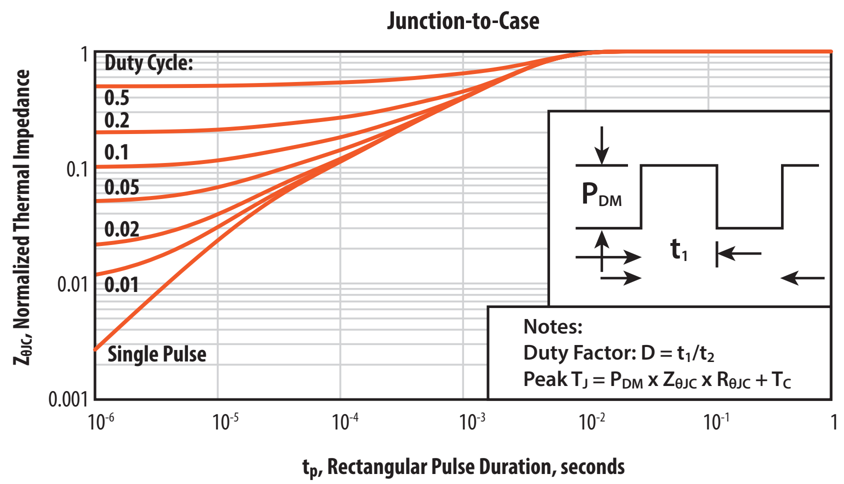
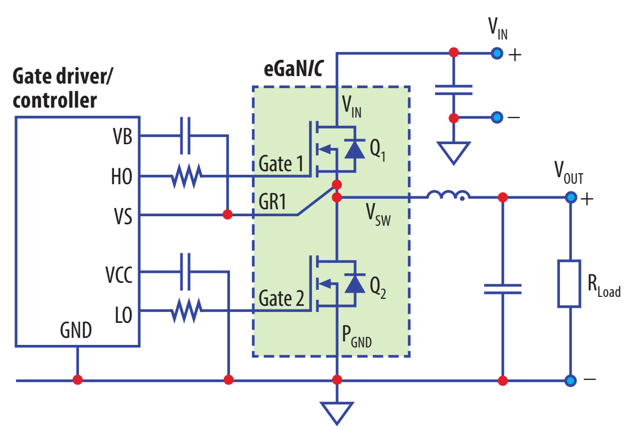
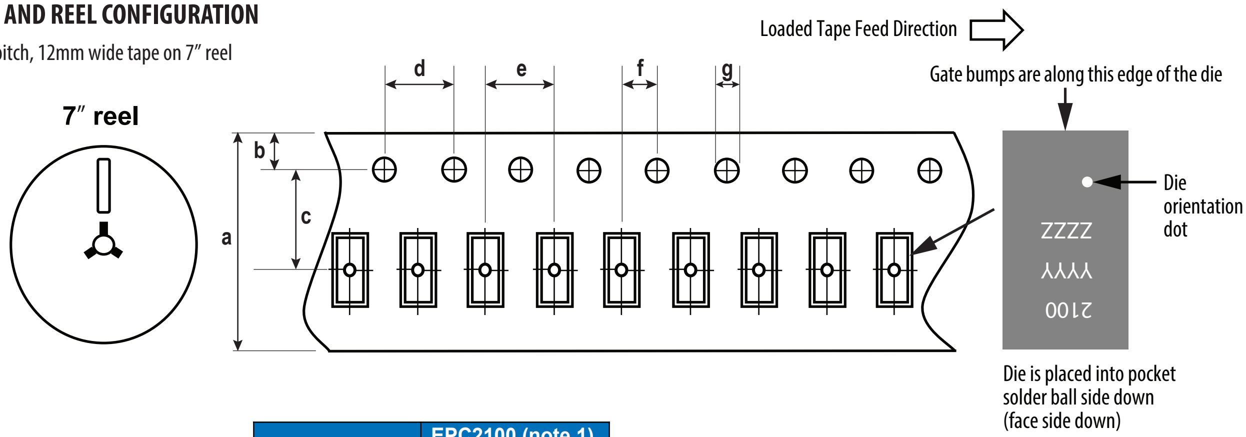


Figure 13
Typical Application Circuit



TAPE AND REEL CONFIGURATION

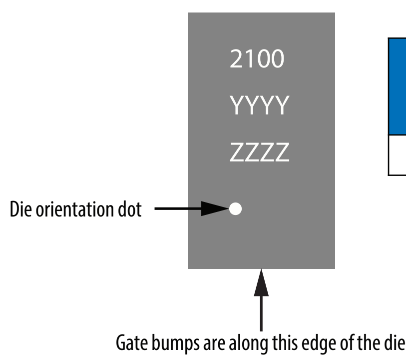
4mm pitch, 12mm wide tape on 7″ reel



	EPC2100 (note 1)		
Dimension (mm)	target	min	max
a	12.00	11.70	12.30
b	1.75	1.65	1.85
c (see note)	5.50	5.45	5.55
d	4.00	3.90	4.10
e	4.00	3.90	4.10
f (see note)	2.00	1.95	2.05
g	1.50	1.50	1.60

Note 1: MSL 1 (moisture sensitivity level 1) classified according to IPC/JEDEC industry standard.
Note 2: Pocket position is relative to the sprocket hole measured as true position of the pocket, not the pocket hole.

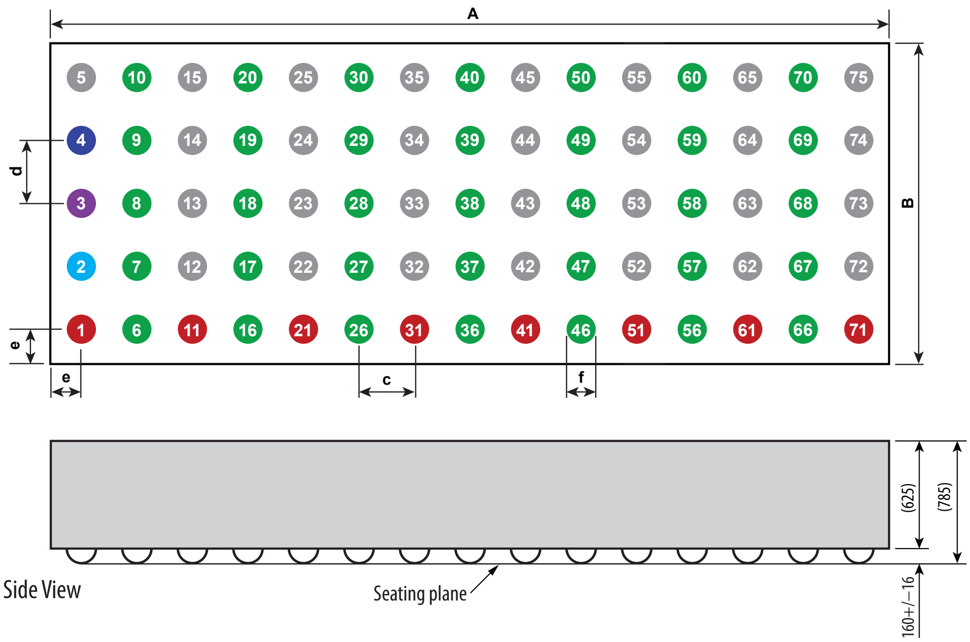
DIE MARKINGS



Part Number	Laser Markings		
	Part # Marking Line 1	Lot_Date Code Marking Line 2	Lot_Date Code Marking Line 3
EPC2100	2100	YYYY	ZZZZ

DIE OUTLINE

Solder Bump View



DIM	MIN	Nominal	MAX
A	6020	6050	6080
B	2270	2300	2330
c	400	400	400
d	450	450	450
e	210	225	240
f	187	225	240

Pad 2 is Gate1 (high side); Pad 4 is Gate2 (low side); Pad 3 is HS Gate Return;

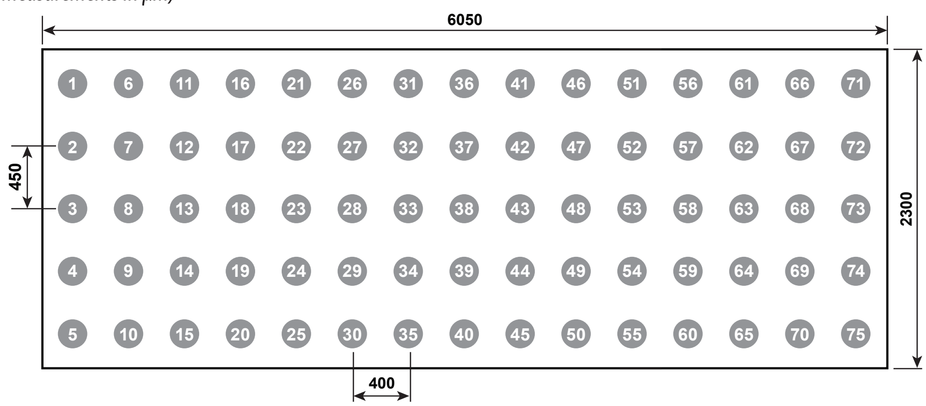
Pads 5, 12, 13, 14, 15, 22, 23, 24, 25, 32, 33, 34, 35, 42, 43, 44, 45, 52, 53, 54, 55, 62, 63, 64, 65, 72, 73, 74, 75 are Ground;

Pads 1, 11, 21, 31, 41, 51, 61, 71 are V_{IN};

Pads 6, 7, 8, 9, 10, 16, 17, 18, 19, 20, 26, 27, 28, 29, 30, 36, 37, 38, 39, 40, 46, 47, 48, 49, 50, 56, 57, 58, 59, 60, 66, 67, 68, 69, 70 are Switch Node

RECOMMENDED LAND PATTERN

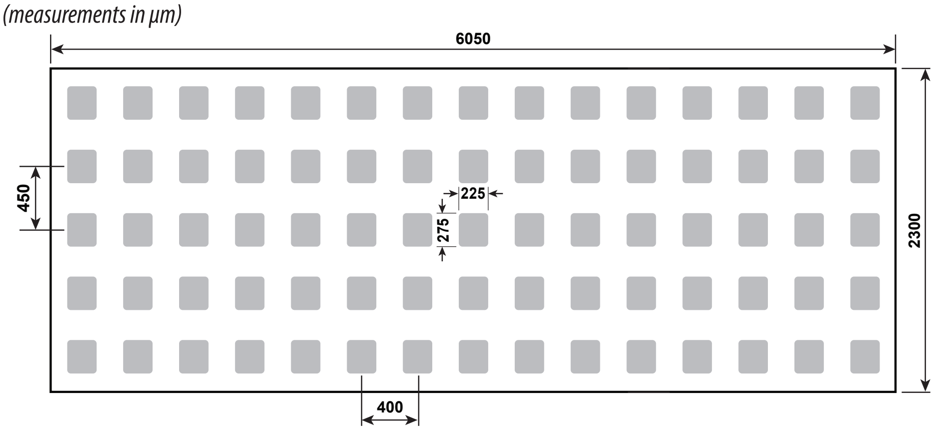
(measurements in µm)



The land pattern is solder mask defined. Suggest SMD Pads at 200 +20/−10 µm. 190 µm minimum.

RECOMMENDED STENCIL DRAWING

(measurements in µm)



Recommended stencil should be 4 mil (100 µm) thick, must be laser cut, openings per drawing.

Intended for use with SAC305 Type 4 solder, reference 88.5% metals content.

Additional assembly resources available at: http://epc-co.com/epc/DesignSupport/AssemblyBasics.aspx

EPC Patent Listing: epc-co.com/epc/AboutEPC/Patents.aspx

Information subject to change without notice.

Revised November, 2017